

**IRF330-333/IRF730-733
MTM/MTP5N35/5N40
N-Channel Power MOSFETs,
5.5 A, 350 V/400 V**

Power And Discrete Division

Description

These devices are n-channel, enhancement mode, power MOSFETs designed especially for high voltage, high speed applications, such as off-line switching power supplies, UPS, AC and DC motor controls, relay and solenoid drivers.

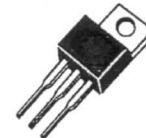
- V_{GS} Rated at ± 20 V
- Silicon Gate for Fast Switching Speeds
- I_{DSS} , $V_{DS(on)}$, SOA and $V_{GS(th)}$ Specified at Elevated Temperature
- Rugged

TO-204AA



IRF330
IRF331
IRF332
IRF333
MTM5N35
MTM5N40

TO-220AB



IRF730
IRF731
IRF732
IRF733
MTP5N35
MTP5N40

Maximum Ratings

Symbol	Characteristic	Rating IRF330/332 IRF730/732 MTM/MTP5N40	Rating IRF331/333 IRF731/733 MTM/MTP5N35	Unit
V_{DSS}	Drain to Source Voltage	400	350	V
V_{DGR}	Drain to Gate Voltage $R_{GS} = 1.0 \text{ M}\Omega$	400	350	V
V_{GS}	Gate to Source Voltage	± 20	± 20	V
T_J, T_{stg}	Operating Junction and Storage Temperature	-55 to +150	-55 to +150	$^{\circ}\text{C}$
T_L	Maximum Lead Temperature for Soldering Purposes, 1/8" From Case for 5 s	275	275	$^{\circ}\text{C}$

Maximum On-State Characteristics

		IRF330/331 IRF730/731	IRF332/333 IRF732/733	MTM5N35/40 MTP5N35/40	
$R_{DS(on)}$	Static Drain-to-Source On Resistance	1.0	1.5	1.0	Ω
I_D	Drain Current Continuous Pulsed	5.5 22	4.5 22	5.0 22	A

Maximum Thermal Characteristics

		1.67	1.67	1.67	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case				
P_D	Total Power Dissipation at $T_C = 25^{\circ}\text{C}$	75	75	75	W



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IRF330-333/IRF730-733

Electrical Characteristics (T_C = 25°C unless otherwise noted)

Symbol	Characteristic	Min	Max	Unit	Test Conditions
Off Characteristics					
V _{(BR)DSS}	Drain Source Breakdown Voltage ¹ IRF330/332/730/732 IRF331/333/731/733	400		V	V _{GS} = 0 V, I _D = 250 μA
		350			
I _{DSS}	Zero Gate Voltage Drain Current		250	μA	V _{DS} = Rated V _{DSS} , V _{GS} = 0 V
			1000	μA	V _{DS} = 0.8 x Rated V _{DSS} , V _{GS} = 0 V, T _C = 125°C
I _{GSS}	Gate-Body Leakage Current IRF330-333 IRF730-733		± 100 ± 500	nA	V _{GS} = ± 20 V, V _{DS} = 0 V
On Characteristics					
V _{GS(th)}	Gate Threshold Voltage	2.0	4.0	V	I _D = 250 μA, V _{DS} = V _{GS}
R _{DS(on)}	Static Drain-Source On-Resistance ² IRF330/331/730/731 IRF332/333/732/733			Ω	V _{GS} = 10 V, I _D = 3.0 A
			1.0		
			1.5		
g _{fs}	Forward Transconductance	3.0		S (Ω)	V _{DS} = 10 V, I _D = 3.0 A
Dynamic Characteristics					
C _{iss}	Input Capacitance		900	pF	V _{DS} = 25 V, V _{GS} = 0 V f = 1.0 MHz
C _{oss}	Output Capacitance		300	pF	
C _{rss}	Reverse Transfer Capacitance		80	pF	
Switching Characteristics (T_C = 25°C, Figures 12, 13)					
t _{d(on)}	Turn-On Delay Time		30	ns	V _{DD} = 175 V, I _D = 3.0 A V _{GS} = 10 V, R _{GEN} = 15 Ω R _{GS} = 15 Ω
t _r	Rise Time		35	ns	
t _{d(off)}	Turn-Off Delay Time		55	ns	
t _f	Fall Time		35	ns	
Q _g	Total Gate Charge		30	nC	V _{GS} = 10 V, I _D = 7.0 A V _{DD} = 180 V
Source-Drain Diode Characteristics					
V _{SD}	Diode Forward Voltage IRF330/331/730/731 IRF332/333/732/733		1.6	V	I _S = 5.5 A; V _{GS} = 0 V
			1.5	V	I _S = 4.5 A; V _{GS} = 0 V
t _{rr}	Reverse Recovery Time	400		ns	I _S = 5.5 A; di _S /dt = 100 A/μS

MTM/MTP5N35/5N40

Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Characteristic	Min	Max	Unit	Test Conditions
Off Characteristics					
$V_{(BR)DSS}$	Drain Source Breakdown Voltage ¹ MTM/MTP5N40 MTM/MTP5N35	400		V	$V_{GS} = 0\text{ V}$, $I_D = 5.0\text{ mA}$
		350			
I_{DSS}	Zero Gate Voltage Drain Current		0.25	mA	$V_{DS} = 0.85 \times \text{Rated } V_{DSS}$, $V_{GS} = 0\text{ V}$
			2.5	mA	$V_{DS} = 0.85 \times \text{Rated } V_{DSS}$, $V_{GS} = 0\text{ V}$, $T_C = 100^\circ\text{C}$
I_{GSS}	Gate-Body Leakage Current		± 500	nA	$V_{GS} = \pm 20\text{ V}$, $V_{DS} = 0\text{ V}$
On Characteristics					
$V_{GS(th)}$	Gate Threshold Voltage	2.0	4.5	V	$I_D = 1.0\text{ mA}$, $V_{DS} = V_{GS}$
		1.5	4.0	V	$I_D = 1.0\text{ mA}$, $V_{DS} = V_{GS}$, $T_C = 100^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance ²		1.0	Ω	$V_{GS} = 10\text{ V}$, $I_D = 2.5\text{ A}$
$V_{DS(on)}$	Drain-Source On-Voltage ²		2.5	V	$V_{GS} = 10\text{ V}$; $I_D = 2.5\text{ A}$
			6.2	V	$V_{GS} = 10\text{ V}$, $I_D = 5.0\text{ A}$
			5.0	V	$V_{GS} = 10\text{ V}$, $I_D = 2.5\text{ A}$, $T_C = 100^\circ\text{C}$
g_{fs}	Forward Transconductance	2.0		S (Ω)	$V_{DS} = 10\text{ V}$, $I_D = 2.5\text{ A}$
Dynamic Characteristics					
C_{iss}	Input Capacitance		1200	pF	$V_{DS} = 25\text{ V}$, $V_{GS} = 0\text{ V}$ $f = 1.0\text{ MHz}$
C_{oss}	Output Capacitance		300	pF	
C_{rss}	Reverse Transfer Capacitance		80	pF	
Switching Characteristics ($T_C = 25^\circ\text{C}$, Figures 12, 13)³					
$t_{d(on)}$	Turn-On Delay Time		50	ns	$V_{DD} = 25\text{ V}$, $I_D = 2.5\text{ A}$ $V_{GS} = 10\text{ V}$, $R_{GEN} = 50\ \Omega$ $R_{GS} = 50\ \Omega$
t_r	Rise Time		100	ns	
$t_{d(off)}$	Turn-Off Delay Time		200	ns	
t_f	Fall Time		100	ns	
Q_g	Total Gate Charge		30	nC	$V_{GS} = 10\text{ V}$, $I_D = 7.0\text{ A}$ $V_{DD} = 180\text{ V}$

Notes

1. $T_J = +25^\circ\text{C}$ to $+150^\circ\text{C}$
2. Pulse test: Pulse width $\leq 80\ \mu\text{s}$, Duty cycle $\leq 1\%$
3. Switching time measurements performed on LEM TR-58 test equipment.